

Surface Mount TVS For ESD Protection Diode

 **Lead(Pb)-Free**

Features:

- * Stand-off Voltage : 5.0V
- * Low Leakage
- * Response Time is Typically < 1 ns
- * ESD Rating of Class 3 (> 16 kV) per Human Body Model
- * IEC61000-4-2 Level 4 ESD Protection
- * IEC61000-4-4 Level 4 EFT Protection
- * These are Pb-Free Devices

Main Applications:

- * Cellular Handsets & Accessories
- * Personal Digital Assistants (PDAs)
- * Notebooks & Handhelds
- * Portable Instrumentation
- * Digital Cameras
- * Peripherals
- * MP3 Players

Mechanical Characteristics:

- * Molding compound flammability rating: UL 94V-0

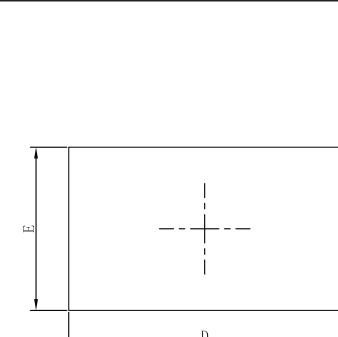
**Total Power Dissipation
100m Watts
Reverse Working Voltage
5.0 Volts**



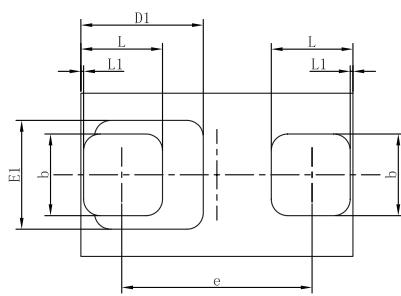
BFBP-02C

BFBP Outline Dimensions

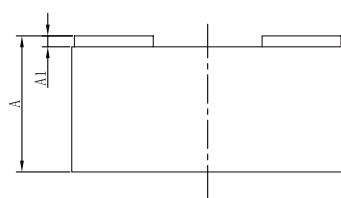
Unit:mm



TOP VIEW



BOTTOM VIEW



SIDE VIEW

Symbol	Min	Max
A	0.450	0.550
A1	0.010	0.070
D	0.950	1.050
E	0.550	0.650
D1	0.450 Ref.	
E1	0.400 Ref.	
b	0.275	0.325
e	0.675	0.725
L	0.275	0.325
L1	0.010 Ref.	

Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

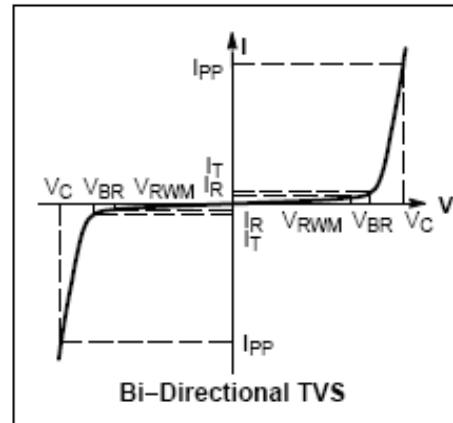
Parameter	Symbol	Limits	Unit
IEC61000-4-2(ESD) Air/Contact		± 30	kV
ESD voltage per human body model		16	kV
Per machine model		400	V
Total power dissipation on FR-5 board (Note 1)	P_D	100	mW
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	1250	°C/W
Lead Solder Temperature – Maximum (10 Second Duration)	T_L	260	°C
Junction and Storage temperature range	T_j, T_{stg}	-55 ~ +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0 x 0.75 x 0.62 in.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
C	Max. Capacitance @ $V_R=0$ and $f = 1\text{MHz}$



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Device	Device Marking	V_{RWM} (V)	I_R (μA) @ V_{RWM}	V_{BR} (V) @ I_T (Note 2)		I_T	V_C @ $I_{PP} = 5\text{ A}$	I_{PP} (A)	V_c (V) @ Max I_{PP}	C (pF)
		Max	Max	Min	Max	mA	V	Max	Max	Max
DTESDB5V0LED02	EB	5.0	1.0	5.8	7.8	1.0	10	11.2	12.5	30

2. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C .